

substrate. The shallow trench isolation 2, an insulated area, can be regarded and called as a field area.

In the Abstract:

Please amend the Abstract as follows:

The object of the present invention is to provide a A semiconductor device is provided including a circuit employing two or more field-effect transistors that are desired to have equal characteristics, capable of realizing high reliability and superior transistor characteristics. The transistors which are desired to have equal characteristics are placed in the semiconductor device so as to have the same STI trench width (the width of shallow trench isolation adjacent to an active area in which the transistor is formed). By such composition, stress growing in the active area due to the shallow trench isolation is equalized among the transistors, and, thereby, the characteristics of the transistors can be equalized.